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ABSTRACT: ABSTRACT OF THE DISCLOSURE

For the protection of an integrated circuit against ESD, it is known to use a Silicon-Controlled Rectifier (SCR), provided with a gated diode or MOS transistor at the periphery of the well to obtain a low trigger voltage. In accordance with the invention, the said gated diode or MOS transistor, located between the anode and the cathode of the SCR, is provided only along a part of the periphery of the SCR, a part of the SCR thus being free from the said gated diode. As a result of this structure, the holding voltage of the SCR is reduced considerably, leading to an important decrease of the dissipation during the ESD event.

*A* ~~Fig. 2.~~